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Ain Shams University
Faculty of Girls
For
Arts, Science and Education

STRUCTURE AND PHYSICAL PROPERTIES OF CADMIUM GALOSELENIDE FILMS AND THE OPTIMUM CONDITIONS FOR SUITABLE ELECTRONIC APPLICATIONS

A Thesis

Submitted For The Ph.D. Degree of Philosophy
In Science (Physics)

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CONTENTS

PAGE

LIST OF FIGURES

LIST OF TABLES

ACKNOWLEDGEMENT

ABSTRACT

SUMMARY

CHAPTER I : INTRODUCTION AND LITERATURE REVIEW

1.1) Introduction 1

1.2) Growth of $CdGa_2Se_4$ Crystals 3

1.3) Structural Characterization of $CdGa_2Se_4$ 4

1.4) Aspects of The Band Structure of $CdGa_2Se_4$ 5

1.5) Optical Properties of $CdGa_2Se_4$ 9

1.6) Transport Properties of $CdGa_2Se_4$ 16

CHAPTER II : THEORETICAL BACKGROUND

2.1) Structure Features of $A^{II}B_2^{III}B_4^{IV}$ Compounds 22

2.1.1- Structure Features of $CdGa_2Se_4$ 26

2.2) Theoretical Determination of the optical constants of thin films 26

a- Bennett and Booty method 28

b- Abelés and Théye's method 29

c- Algebraic inversion methods. 30

d- Envelope methods 30

2.3) Activation Energies For Electronic Conduction 31

2.3.1- Intrinsic Semiconductor 31

2.3.2- Extrinsic Semiconductor 32

I- Uncompensated Case 32

II- Compensated Case 33

2.3.3- Pseudo-Intrinsic or non-extrinsic conduction 35

2.3.4- Meyer-Neldel rule 37

2.4) Thermoelectric Power 39

2.5) Heterojunctions 40

CHAPTER III : EXPERIMENTAL TECHNIQUES

3.1) Preparation of $CdGa_2Se_4$ in Bulk form 44

3.2) Preparation of Thin Films of $CdGa_2Se_4$ 45

3.2.1- Cleaning of the substrate surface. 48

3.2.2- Deposition technique 48

3.3) Film Thickness Measurement 50

3.1.1- Quartz crystal thickness monitor 50

3.3.2- Multiple beam interferometry 51

3.3.3- Envelope method 53

3.4) Structure Characterization Techniques 55

3.4.1- X-ray diffraction 55

3.4.2- Electron microscopy technique 56

3.4.2.1- Preparation of $CdGa_2Se_4$ thin films for electron microscope examination 56

3.5) Determination of The Optical Constants of Absorping Films on Transparent Substrates 57

3.5.1- The transmittance at normal light incidence 58

3.5.2- The reflectance at normal light incidence 58

3.5.3- Computing the optical constants of thin films. 59

3.6) Electrical Resistivity Measurements 64

3.7) Thermoelectric Power Measurements 65

3.8) $CdGa_2Se_4$ /Si Heterojunctions 69

3.8.1- Preparation of $CdGa_2Se_4$ /Si heterojunctions 69

3.8.2- Current-voltage measurements of heterojunctions 69

CHAPTER IV : STRUCTURE CHARACTERIZATION OF $CdGa_2Se_4$

4.1) Structure Investigation of $CdGa_2Se_4$ Ingot Material 71

4.2) Structure Characterization of As-deposited $CdGa_2Se_4$ Thin Films 77

4.3) Effect of Heat Treatment on the Structure Characterization of $CdGa_2Se_4$ Thin Films 82

4.4) Effect of Heat Treatment on the Crystallite Size of $CdGa_2Se_4$ Thin Films 87

CHAPTER V : OPTICAL PROPERTIES OF $CdGa_2Se_4$ THIN FILMS

5.1) The Spectral Distribution of Transmittance and Reflectance 99

5.2) The Spectral Distribution of Absorption Coefficient 103

5.3) The Spectral Distribution of the Refractive Index and the Dielectric Constant. 109

CHAPTER VI : TRANSPORT PROPERTIES OF $CdGa_2Se_4$ THIN FILMS

6.1) The Electrical Conductivity of $CdGa_2Se_4$ Thin Films 116

6.1.1- Current-voltage characteristics of $CdGa_2Se_4$ thin films 116

6.1.2- The volume and surface conductivities of $CdGa_2Se_4$ thin films 120

6.1.3- The electrical conductivity of $CdGa_2Se_4$ in bulk form 123

6.1.4- The effect of thickness on the surface electrical conductivity of $CdGa_2Se_4$ thin films 126

6.1.5- The effect of annealing on surface electrical conductivity of $CdGa_2Se_4$ thin films 131

6.2) The Thermoelectric Power of $CdGa_2Se_4$ Thin Films 137

6.3) The Electrical Characteristics of p-$CdGa_2Se_4$/n-Si Heterojunctions 145

GENERAL CONCLUSIONS 162

REFERENCES 168

ARABIC SUMMARY

LIST OF FIGURES

Fig. (1.1) : The model of the valence band of $CdGa_2Se_4$ at the Γ point of the Brillouin zone (Δ_{so} : spin-orbit interaction).

Fig. (1.2) : Transmission spectra of $CdGa_2Se_4$ grown from different starting materials (a) and two binary compounds of CdSe and Ga_2Se_3 with stoichiometric or nonstoichiometric compositions (b).

Fig. (1.3) : Temperature dependence of electrical conductivity and thermo-electric power for $CdGa_2Se_4$ single crystal.

Fig. (2.1) : Chalcopyrite family and related compounds in which the individual atomic species may be replaced by others of similar valence.

Fig. (2.2) : Defect chalcopyrite structure of $CdGa_2Se_4$.

Fig. (2.3) : Schematic energy level diagram for a solid in which the dominant electron and hole states are labelled (m) and (q) respectively.

Fig. (2.4) : (a) Energy-band diagram for two isolated n- and p-type semiconductors.

(b) Energy -band diagram of p-n heterojunction at equilibrium according to Anderson model.

Fig. (3.1) : Rotating furnace.

Fig. (3.2) : Schematic diagram of coating system.

Fig. (3.3) : Typical interferometer arrangement.

Fig. (3.4) : Schematic diagram of multiple-beam interferometry.

Fig. (3.5) : Fringes produced by multiple-beam interferometry across a film substrate step.

Fig. (3.6) : Simplified optical path of the V-W specular reflection; Schematic (A) in the V case and (B) in the w case.

Fig. (3.7) : Flow chart diagram of the program used for the optical constants calculations.

Fig. (3.8) : Plot of the variance versus refractive index, n for different values of absorption index, k [T_{exp}, R_{exp} and t/λ are kept constant].

Fig. (3.9) : Schematic diagram of the electrical circuit for measuring the film resistance.

Fig. (3.10) : Schematic diagtram of the circuit used for measuring the electromotive force.

Fig. (3.11) : Sketch of $CdGa_2Se_4$ /Si heterojunction.

Fig. (3.12) : The electrical circuit used for measuring the current-voltage characteristics of heterojunction.

Fig. (4.1) : The atomic scattering factor, for (a) Ga, (b) Se and c) Cd element plotted against sin θ/λ.

Fig. (4.2) : (a) The Debye-Scherrer pattern for $CdGa_2Se_4$ in powder form. (b) The calculated relative intensities of X-ray diffraction pattern of $CdGa_2Se_4$ in powder form (CuK_α line was used).

Fig. (4.3) : XRD pattern of as-deposited $CdGa_2Se_4$ film of thickness 580 nm.

Fig. (4.4-6) : Electron microscope diffraction patterns of as-deposited $CdGa_2Se_4$ thin films of thicknesses 30, 40 and 50 nm respectively.

Fig. (4.7-9) : TEM micrograph as-deposited $CdGa_2Se_4$ thin films of thicknesses 30, 40 and 50 nm respectively [magnification = 25000 X].

Fig. (4.10) : XRD patterns of $CdGa_2Se_4$ films of 580 nm thick : (a) as-deposited film; and films annealed at (b) 473 K, (c) 573 K, (d) 623 K, and (e) 673 K, (f) XRD pattern of $CdGa_2Se_4$ in powder form.

Fig. (4.11) : (a-c) XRD patterns of $CdGa_2Se_4$ films of nearly equal thicknesses $\cong$ 270 nm deposited at substrate temperatures of (a) 300 K, (b) 523 K and (c) 573 K, (d) XRD pattern of $CdGa_2Se_4$ in powder form.

Fig. (4.12,13) : Electron microscope diffraction patterns of $CdGa_2Se_4$ film of thickness 35 nm deposited at T_S = 300 K and 573 K respectively.

Fig. (4.14) : X-ray line broadening of the (112) reflection for $CdGa_2Se_4$ in powder form.

Fig. (4.15) : X-ray line broadening of the (112) reflection for $CdGa_2Se_4$ thin film of thickness 580 nm annealed at T_A = 598 K.

Fig. (4.16) : X-ray line boradeining of the (112) reflection for $CdGa_2Se_4$ thin film of thickness 580 nm annealed at T_A = 623 K.

Fig. (4.17) : X-ray line boradening of the (112) reflection for $CdGa_2Se_4$ thin film of thickness 580 nm annealed at T_A = 673 K.

Fig. (4.18) : X-ray line broadening of the (112) reflection for $CdGa_2Se_4$ thin film of thickness 270 nm prepared at T_S = 573 K.

Fig. (4.19,20) : TEM micrographs of $CdGa_2Se_4$ thin film of thickness 35 nm deposited at T_S = 300 and 573 K respectively [magnification = 25000 X].

Fig. (5.1) : The spectral behaviour of the transmittance T(λ) and reflectance R(λ) at normal incidence for as-deposited $CdGa_2Se_4$ films of different thicknesses.

Fig. (5.2) : The spectral behaviour of the transmittance T(λ) and reflectance R(λ) at normal incidence for $CdGa_2Se_4$ films of different thicknesses deposited onto preheated substrates T_S = 573 K.

Fig. (5.3) : The spectral behaviour of the transmittance T(λ) and reflectance R(λ) at normal incidence for $CdGa_2Se_4$ films of different thicknesses and annealed at T_A = 623 K for two hours.

Fig. (5.4) : The spectral distribution of absorption index, k(λ) of $CdGa_2Se_4$ films

(A) as-deposited.

(B) [o] T_A = 623 K (open circle) and [•] T_S = 573 K (solid circle).

Fig. (5.5) : The spectral behaviour of the absorption coefficient, α
(A) as-deposited.
(B) Same as in Fig. 5.4(B).

Fig. (5.6) : $(\alpha h\nu)^{1/2}$ plotted against $(h\nu)$:
(A) as-deposited
(B) Same as in Fig. 5.4(B).

Fig. (5.7) : $(\alpha h\nu)^2$ plotted against $(h\nu)$:
(A) as-deposited
(B) Same as in Fig. 5.4(B).

Fig. (5.8) : Log $(\alpha h\nu)$ plotted against log $(h\nu - E_g)$ for as-deposited $CdGa_2Se_4$ thin films

Fig. (5.9) : The spectral distribution $n(\lambda)$ of $CdGa_2Se_4$ films :
(A) as-deposited
(B) Same as in Fig. 5.4(B).

Fig. (5.10) : $(n^2 - 1)^{-1}$ plotted against λ^{-2} in wavelength range 540-840 nm :
(A) as-deposited
(B) Same as in Fig. 5.4(B).

Fig. (6.1) : Log I vs. Log V for a sample C_1 of thickness 326.8 nm deposited at T_s = 573 K. The measurement was performed for Au/$CdGa_2Se_4$/Au configuration at room temperature.

Fig. (6.2) : Log I vs $V^{1/2}$ in high field region for the sample C_1.

Fig. (6.3a) : The temperature dependence of the conductivity for the sample C_1 in sandwich conrfiguration.

Fig. (6.3b) : The temperature dependence of the condutivity for the sample C_1 in coplanar configuration.

Fig. (6.4) : The temperature dependence of the conductivity for $CdGa_2Se_4$ in bulk form.